

QM150HY-2H

HIGH POWER SWITCHING USE
INSULATED TYPE

QM150HY-2H



- **IC** Collector current **150A**
- **VCEX** Collector-emitter voltage **1000V**
- **hFE** DC current gain **75**
- **Insulated Type**
- **UL Recognized**

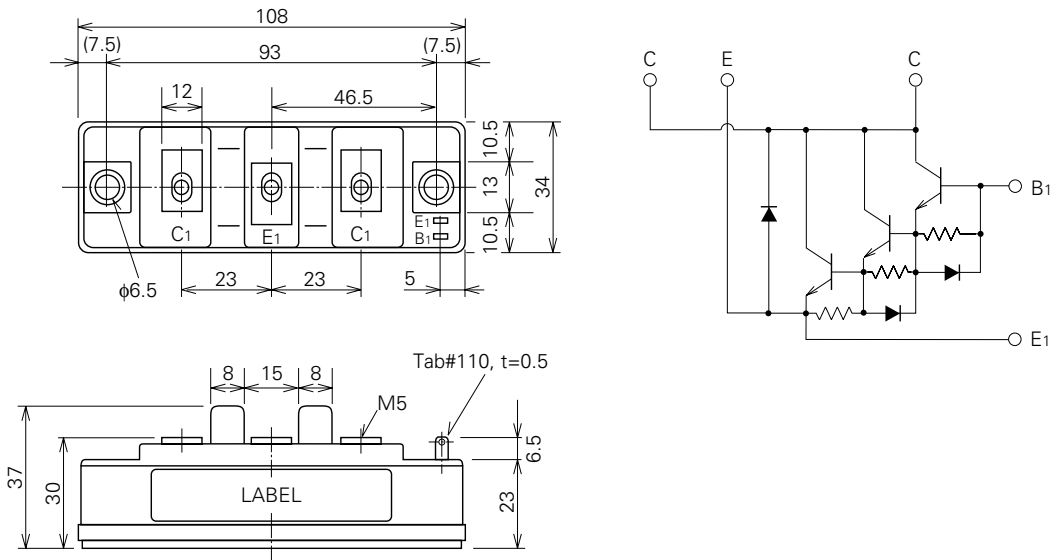
Yellow Card No. E80276 (N)
File No. E80271

APPLICATION

Inverters, Servo drives, DC motor controllers, NC equipment, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



QM150HY-2H

HIGH POWER SWITCHING USE
INSULATED TYPE

ABSOLUTE MAXIMUM RATINGS (T_j=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CEX (SUS)}	Collector-emitter voltage	I _C =1A, V _{EB} =2V	1000	V
V _{CEX}	Collector-emitter voltage	V _{EB} =2V	1000	V
V _{CBO}	Collector-base voltage	Emitter open	1000	V
V _{EBO}	Emitter-base voltage	Collector open	7	V
I _C	Collector current	DC	150	A
-I _C	Collector reverse current	DC (forward diode current)	150	A
P _C	Collector dissipation	T _C =25°C	1000	W
I _B	Base current	DC	8	A
-I _{CSM}	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	1500	A
T _j	Junction temperature		-40~+150	°C
T _{stg}	Storage temperature		-40~+125	°C
V _{iso}	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Main terminal screw M5	1.47~1.96	N·m
			15~20	kg·cm
		Mounting screw M6	1.96~2.94	N·m
			20~30	kg·cm
—	Weight	Typical value	250	g

ELECTRICAL CHARACTERISTICS (T_j=25°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{CEX}	Collector cutoff current	V _{CE} =1000V, V _{EB} =2V	—	—	2.0	mA
I _{CBO}	Collector cutoff current	V _{CB} =1000V, Emitter open	—	—	2.0	mA
I _{EBO}	Emitter cutoff current	V _{EB} =7V	—	—	200	mA
V _{CE (sat)}	Collector-emitter saturation voltage	I _C =150A, I _B =3A	—	—	2.5	V
V _{BE (sat)}	Base-emitter saturation voltage		—	—	3.5	V
-V _{CEO}	Collector-emitter reverse voltage	-I _C =150A (diode forward voltage)	—	—	1.8	V
h _{FE}	DC current gain	I _C =150A, V _{CE} =2.8V/5V	75/100	—	—	—
t _{on}	Switching time	V _{CC} =600V, I _C =150A, I _{B1} =-I _{B2} =3A	—	—	3.0	μs
t _s			—	—	15	μs
t _f			—	—	3.0	μs
R _{th (j-c) Q}	Thermal resistance (junction to case)	Transistor part	—	—	0.125	°C/W
R _{th (j-c) R}		Diode part	—	—	0.6	°C/W
R _{th (c-f)}	Contact thermal resistance (case to fin)	Conductive grease applied	—	—	0.065	°C/W

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Darlington Transistors](#) category:

Click to view products by [Mitsubishi](#) manufacturer:

Other Similar products are found below :

[281287X](#) [SMMBT6427LT1G](#) [2N7371](#) [BDV64B](#) [JANTXV2N6287](#) [028710A](#) [SMMBTA64LT1G](#) [2N6350](#) [2SB1214-TL-E](#)
[SMMBTA14LT1G](#) [SBSP52T1G](#) [NJVMJD117T4G](#) [Jantx2N6058](#) [2N6353](#) [LB1205-L-E](#) [500-00005](#) [2N6053](#) [NJVMJD112G](#) [Jan2N6350](#)
[Jantx2N6352](#) [Jantx2N6350](#) [BULN2803LVS](#) [ULN2001N](#) [2SB1383](#) [2SB1560](#) [2SB852KT146B](#) [TIP112TU](#) [TIP122TU](#) [BCV27](#) [MMBTA13-](#)
[TP](#) [MMBTA14-TP](#) [MMSTA28T146](#) [BSP50H6327XTSA1](#) [KSH122TF](#) [NTE2557](#) [NJVNJD35N04T4G](#) [TIP115](#) [MPSA29-D26Z](#) [MJD127T4](#)
[FJB102TM](#) [BCV26E6327HTSA1](#) [BCV46E6327HTSA1](#) [BCV47E6327HTSA1](#) [BSP61H6327XTSA1](#) [BU941ZPFI](#) [2SB1316TL](#) [2SD1980TL](#)
[NTE2350](#) [NTE245](#) [NTE246](#)